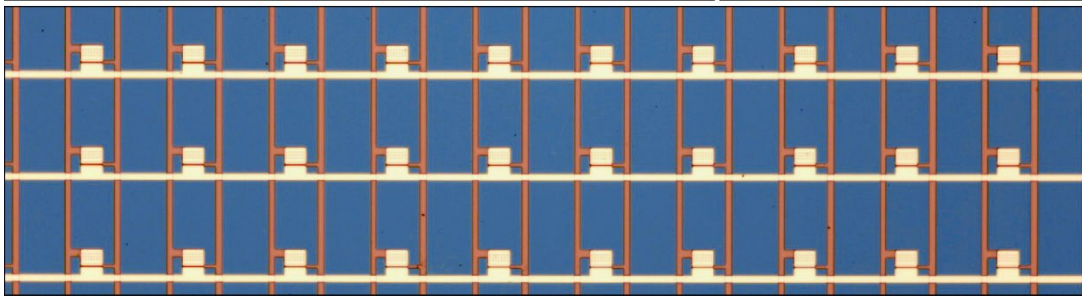
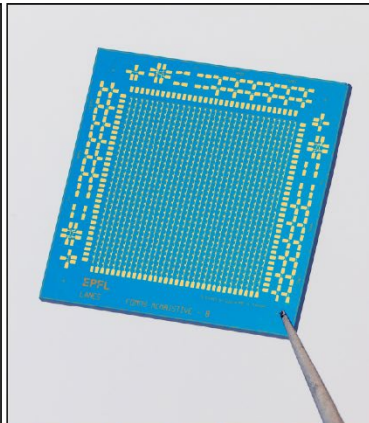
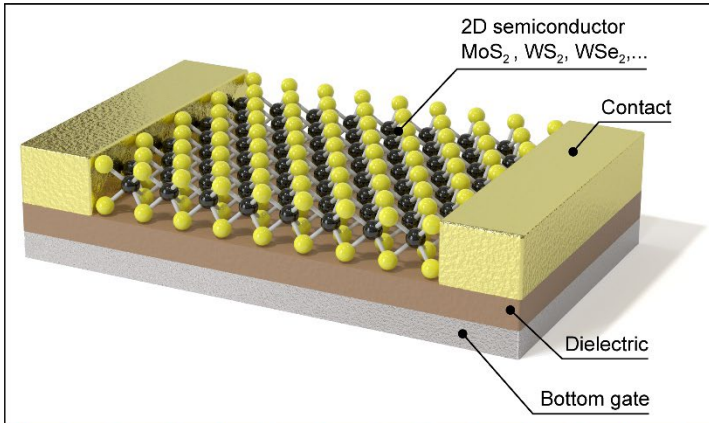


Semiconductor Device



Ref. Nr	6.1022
Keywords	2D semiconductors, scaled logic devices, in-memory computing
Intellectual Property	US20140197459A1
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Exemplary devices and circuits. Upper left: field-effect transistor with a 2D semiconductor as a channel, electrical contacts and a gate electrode. Upper right: Vector matrix multiplier (VMM) processor based on an MOCVD-grown 2D semiconductor, fabricated on wafer scale at EPFL. Lower panel: micrograph of a portion of a VMM circuit produced at EPFL.

Description

2D semiconductors such as MoS₂, WS₂ etc. could be an attractive alternative to silicon for the fabrication of transistors with sub-10 nm gate lengths due to a favorable combination of atomic-scale thickness, presence of a band gap and good electrical properties resulting in reduced power consumption.

The innovation consists of the use of 2D semiconductors in field-effect devices. Exemplary embodiments include field-effect transistors, photodetectors, floating gate memory devices which have recently been included by our group in large-scale integrated vector matrix multipliers.

Advantages

- Suitable for fabrication of scaled semiconductor devices

- Low power consumption due to Excellent electrostatic control and low dielectric constant resulting in reduced power consumption
- Absence of dangling bonds on the surface
- Breaking strain >11%
- Stable up to at least 1000°C in inert atmosphere
- Compatible with semiconductor fabrication processing, wafer scale processing

Applications

- Semiconducting electronics
- Digital electronics

Offering

- Licencing and/or collaboration